

UNITED STATES DEARTMENT OF COMMERCE **Patent and Trademark Offic**

Address: COMMISSIONER OF PATENTS AND TRADEMARKS

Washington, D.C. 20231

APPLICATION NO. **FILING DATE** FIRST NAMED INVENTOR ATTORNEY DOCKET NO. 09/325,951 06/04/99 CHIANG M TSMC98-262 **EXAMINER** MM92/0921 GEORGE SAILE POMPEY,R

20 MCINTOSH DRIVE POUGHKEEPSIE NY 12603

ART UNIT PAPER NUMBER 2812

DATE MAILED:

09/21/00

Pl ase find below and/or attached an Office communication concerning this application or pr ceeding.

Commissioner of Patents and Trademarks

	Application No.	Applicant(s)
Office Action Summary	09/325,951	CHIANG ET AL.
	Examiner	Art Unit
	Ron E Pompey	2812
The MAILING DATE of this communication appears on the cover sheet with the correspondenc address Period for Reply		
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.		
 Extensions of time may be available under the provisions of 37 CFR 1.136 (a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Status 		
1) Responsive to communication(s) filed on		
2a) This action is FINAL . 2b) This action is non-final.		
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.		
Disposition of Claims		
4) Claim(s) 1-10 is/are pending in the application.		
4a) Of the above claim(s) is/are withdrawn from consideration.		
5) Claim(s) is/are allowed.		
6)⊠ Claim(s) <u>1-10</u> is/are rejected.		
7) Claim(s) is/are objected to.		
8) Claims are subject to restriction and/or election requirement.		
Application Papers		
9) The specification is objected to by the Examiner.		
10) The drawing(s) filed on is/are objected to by the Examiner.		
11) ☐ The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved.		
12) The oath or declaration is objected to by the Examiner.		
Priority under 35 U.S.C. § 119		
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d).		
a) ☐ All b) ☐ Some * c) ☐ None of the CERTIFIED copies of the priority documents have been:		
1. received.		
2. received in Application No. (Series Code / Serial Number)		
3. received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).		
* See the attached detailed Office action for a list of the certified copies not received.		
14) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. & 119(e).		
Attachment(s)		
15) ⊠ Notice of References Cited (PTO-892) 16) □ Notice of Draftsperson's Patent Drawing Review (PTO-948) 17) ⊠ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 2	19) Notice of Informal	ry (PTO-413) Paper No(s) Patent Application (PTO-152)



Application/Control Number: 09/325,951

Art Unit: 2812

DETAILED ACTION

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1-2 and 4 are rejected under 35 U.S.C. 102(b) as being anticipated by Liu et al. (US 5,739,063).

Liu discloses the steps of:

For claims 1-2 and 4:

oxidizing the silicon semiconductor substrate locally at a first oxidation temperature of at least above 1100 degrees centigrade through the silicon nitride mask pattern to form silicon oxide dielectric layers (col. 6, Ins. 27-34).

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Application/Control Number: 09/325,951

Art Unit: 2812

4. Claims 3, 5-10 rejected under 35 U.S.C. 103(a) as being unpatentable over Higashitani et al. (US 5,637,528) in view of Wolf (Siliocn Processing for the VLSI Era, Vol. 1, pg. 209-10).

Higashitani discloses the steps of:

For claims 6-8:

oxidizing the silicon substrate locally at a first temperature of at least above 1100 degrees centigrade through the patterned silicon nitride mask layer to form silicon oxide dielectric field oxide (FOX) isolation layers (col. 5, lns. 5-10).

Higashitani fails to disclose some or all the limitations of claims 6-8. However, Wolf is applied supra as to claim 6, discloses the steps of:

For claims 6-8:

oxidizing the silicon substrate further at a second temperature no greater than 1100 degrees centigrade (pg. 209-10, section-titled growth of thin oxides).

Therefore, it would have been obvious to a person of ordinary skill in the art at the time the invention was made to combine the steps of Wolf in Higashitani because oxidizing under lower temperature forms a more reliable gate oxide.

The examiner would also like to note that the limitations of claims 3, 5 and 9-10 are conventional, substrate materials, dry environment conditions and crystal orientations, in semiconductor processing of today.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ron E Pompey whose telephone number is (703) 305-3016. The examiner can normally be reached on 9 hour days.

Application/Control Number: 09/325,951

Art Unit: 2812

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (703) 308-3325. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 305-3432 for regular communications and (703) 305-3432 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Ron Pompey

Art Unit: 2812

September 19, 2000

John F. Niebling Supervisory Patent Examiner Technology Center 2800